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Interface properties of O₂ annealed Au/Ni/n-AlGaN and Ir/n-AlGaN Schottky barrier systems

We systematically annealed Ni/Au and Ir Schottky contacts on Al_{0.35}Ga_{0.65}N in O₂. Our Capacitance-Voltage-Frequency (C-V-f) measurements reveal the presence of anomalous peaks at 0.9V for Au/Ni/Al_{0.35}Ga_{0.65}N and at 0.8V and 1.2V for the Ir/Al_{0.35}Ga_{0.65}N contact system. The overall quality of both Schottky systems improves with O₂ annealing up to 573K.

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